

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Simon DELEONIBUS et al.

Application No.: 10/594,222

Filed: November 8, 2006

Docket No.: 129558

For: SEMICONDUCTOR-ON-INSULATOR SUBSTRATE COMPRISING A BURIED
DIAMOND-LIKE LAYER AND METHOD FOR MAKING SAME

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

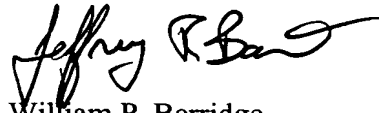
Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of one or more non-English language reference is discussed in the present specification. See References 8 and 9.
- ☒ 3. One or more reference cited herein was cited in a counterpart foreign application. An English language version of the French Search Report is attached for the Examiner's information. See References 1, 2 and 8 - 10.
- ☒ 4. One or more reference cited herein was cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information. See References 6, 7, 11 and 12.
- ☒ 5. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- ☒ 6. A concise explanation of the relevance of one or more non-English language reference cited herein appears in the Appendix attached hereto. See Reference 10.

- ☒ 7. An English language Abstract of one or more non-English language reference is attached hereto. See References 8 - 10 and 12.
- ☒ 8. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and is attached, but has not been reviewed for accuracy. See Reference 12.
- ☒ 9. Reference 3 corresponds to reference 10.
Reference 5 corresponds to reference 8.

Respectfully submitted,



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<p>DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461</p>
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Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 129558		APPLICATION NO. 10/594,222	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Simon DELEONIBUS et al.			
				FILING DATE November 8, 2006			
U.S. PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Name			
	1	5,863,324 A	01/26/1999	KOBASHI et al.			
	2	5,743,957 A	04/28/1998	KOBASHI			
	3	5,714,395 A	02/03/1998	BRUEL			
	4	5,366,923 A	11/22/1994	BEYER et al.			
	5	2003/219959 A1	11/27/2003	GHYSELEN et al.			
	6	2002/140031 A1	10/03/2002	RIM			
	7	2004/023468 A1	02/05/2004	GHYSELEN et al.			
FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation	
	8	WO 02/43124 A2	05/30/2002	WIPO	X		
	9	DE 44 23 067 A1	01/04/1996	GERMANY	X		
	10	EP 0 763 849 A1	03/19/1997	EUROPE	X		
	11	EP 0 570 321 A2	11/18/1993	EUROPE			
	12	JP A 2001-094144	04/06/2001	JAPAN	X	X	
OTHER DOCUMENTS							
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)					
	13	Nakayama, Hajime, et al. "SOI MOSFET Thermal Conductance and Its Geometry Dependence." IEEE International SOI Conference, pp. 128 - 129, October 2000.					
EXAMINER				DATE CONSIDERED			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: November 8, 2006

APPENDIX

Brief description of a non-English document cited in the French search report:

EP0763849 describes separation (figures 3 and 4) of a thin film 18 from a semi-conducting wafer 10/20, using ion implantation. A rigid layer 22 is formed on the wafer 10 before ion implantation. The material of the rigid layer 22 is silicon carbide SiC or diamond. The diamond material is chosen for its mechanical properties and for its simplicity of deposition. Furthermore hydrogen ions can easily traverse a diamond layer.